

ABSTRACT OF THE DISCLOSURE

A silicon carbide (SiC) substrate is provided with an off-oriented {0001} surface whose off-axis direction is $\langle 11-20 \rangle$. A trench is formed on the SiC to have a stripe structure extending toward a $\langle 11-20 \rangle$ direction. An SiC epitaxial layer is formed on an inside surface of the trench.

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